

### KSE5740/5741/5742

# **High Voltage Power Switching In Inductive Circuits**

- High Voltage Power Darlington TR
- Small Engine Ignition
- · Switching Regulators
- Inverters
- Solenold and Relay Drivers
- Motor Control



1.Base 2.Collector 3.Emitter

### **NPN Silicon Darlington Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
BV <sub>CEO</sub> (sus)	Collector-Emitter Sustaining Voltage		
	: KSE5740	300	V
	: KSE5741	350	V
	: KSE5742	400	V
V <sub>CEV</sub>	Collector-Emitter Voltage: KSE5740	600	V
	: KSE5741	700	V
	: KSE5742	800	V
V <sub>EBO</sub>	Emitter-Base Voltage	8	V
I <sub>C</sub>	Collector Current (DC)	8	А
I <sub>CP</sub>	*Collector Current (Pulse)	16	Α
I <sub>B</sub>	Base Current (DC)	2.5	А
I <sub>BP</sub>	*Base Current (Pulse)	5	А
P <sub>C</sub>	Collector Dissipation	80	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)	Collector-Emitter Sustaining Voltage : KSE5740 : KSE5741 : KSE5742	I <sub>C</sub> = 50mA, I <sub>B</sub> =0	300 350 400			V V V
I <sub>CEV</sub>	Collector Cut-off Current	V <sub>CEV</sub> =Rate Value, V <sub>BE(OFF)</sub> =1.5V			1	mA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = 8V, I <sub>C</sub> = 0			75	mA
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.5A$ $V_{CE} = 5V, I_{C} = 4A$	50 200	100 400		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =4A, I <sub>B</sub> = 0.2A I <sub>C</sub> =8A, I <sub>B</sub> = 0.4A			2	V V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> =4A, I <sub>B</sub> = 0.2A I <sub>C</sub> =8A, I <sub>B</sub> = 0.4A			2.5 3.5	V V
V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> =5A			2.5	V
t <sub>D</sub>	Delay Time	$V_{CC} = 250V, I_{C}(pk) = 6A$		0.04		μs
t <sub>R</sub>	Rise Time	$I_{B1} = I_{B2} = 0.25A$		0.5		μs
t <sub>S</sub>	Storage Time	$t_p = 25\mu s$		8		μs
t <sub>F</sub>	Fall Time	Duty Cycle≤1%		2		μs
t <sub>SV</sub>	Voltage Storage Time	$I_{C}(pk) = 6A, V_{CE}(pk) = 250V$		4		μs
t <sub>C</sub>	Cross-over Time	$I_B 1 = 0.06A, V_{BE} (off) = 5V$		2		μs

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## **Typical Characteristics**

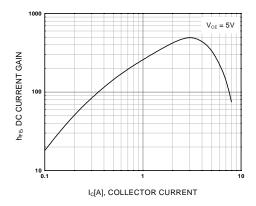


Figure 1. DC current Gain

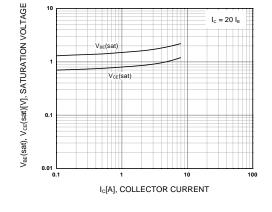


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

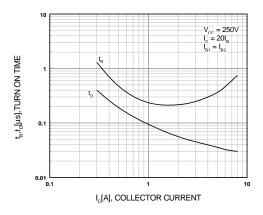


Figure 3. Turn On Time

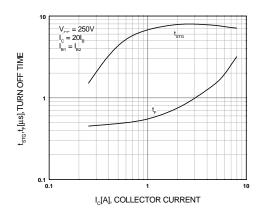


Figure 4. Turn Off Time

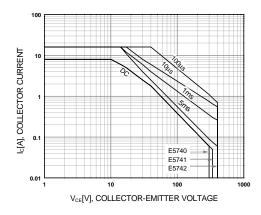


Figure 5. Safe Operating Area

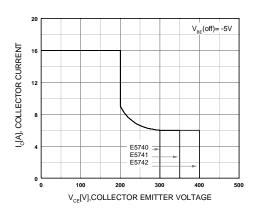


Figure 6. Reverse Bias Safe Operating Area

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## Typical Characteristics (Continued)

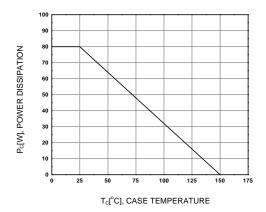
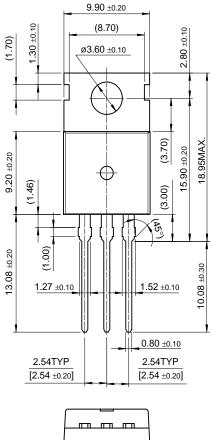
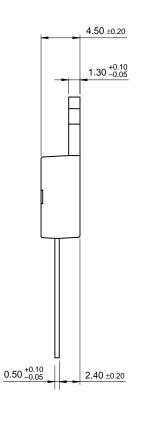


Figure 1. Power Derating

## **Package Demensions**

## TO-220





10.00 ±0.20

Dimensions in Millimeters

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